

[illegible]

The present invention includes the steps of depositing an inducing substance for silicon crystallization on an amorphous silicon layer by plasma exposure, and carrying out annealing on the amorphous silicon layer to the amorphous silicon layer. The present invention includes a chamber having an inner space, a substrate support in the chamber wherein the substrate support supports a substrate, a plasma generating means in the chamber wherein the plasma generating means produces plasma inside the chamber, and a heater at the substrate support wherein the heater supplies the substrate with heat.